



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOD-123 封装二极管/SOD-123 Plastic-Encapsulate Diodes

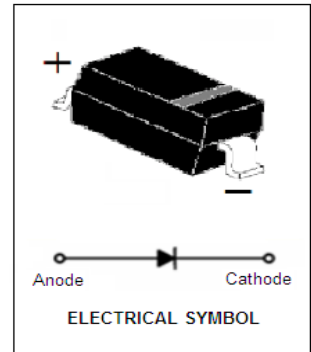
SD103AW/SD103BW/SD103CW (SCHOTTKY DIODES)

特点/Features :

- 正向导通电压低；
- 环保护结构提供瞬态保护；
- 极小的恢复时间；
- 极小的反向电容；

用途/Applications :

高速开关电路。



极限参数/Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	SD103AW	SD103BW	SD103CW	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	40	30	20	V
Working Peak Reverse Voltage	V_{RWM}				
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	I_{FM}	350			mA
Non-repetitive Peak Forward Current (@t≤1S)	I_{FSM}	2			A
Power Dissipation	P_d	400			mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$	250			°C/mW
Junction Temperature	T_j	125			°C
Storage Temperature	T_{stg}	-55~150			°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最小值	典型值	最大值	单位
Reverse Breakdown Voltage SD103AW SD103BW SD103CW	$V_{(BR)R}$	$I_R=100 \mu A$ $I_R=100 \mu A$ $I_R=100 \mu A$	40 30 20			V
Forward Voltage	V_F	$I_F=20mA$			0.37	V
		$I_F=200mA$			0.60	V
Reverse Current SD103AW SD103BW SD103CW	I_{RM}	$V_R=30V$ $V_R=20V$ $V_R=10V$			5.0	μA
Capacitance Between Terminals	C_T	$V_R=0V, f=1.0MHz$		50		pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=200mA,$ $I_{rr}=0.1 \times I_R, R_L=100 \Omega$		10		nS

印章/ Marking:

型号	SD103AW	SD103BW	SD103CW
印章	S4	S5	S6



典型特性曲线图/Typical Characteristics

